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FDS6576

P-Channel 2.5V Specified PowerTrench® MOSFET **General Description Features**

This P-Channel 2.5V specified MOSFET is in a rugged gate version of Fairchild Semiconductor's advanced PowerTrench® process. It has been optimized for power management applications with a wide range of gate drive voltage (2.5V - 12V).

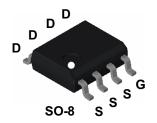
Applications

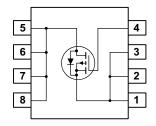
- Load switch
- Battery protection
- Power management



$-11 \text{ A}, -20 \text{ V}. \text{ R}_{DS(ON)} = 0.014 \Omega \text{ @ V}_{GS} = -4.5 \text{ V}$ $R_{DS(ON)} = 0.020 \Omega @ V_{GS} = -2.5 V$

- Extended V_{GSS} range (±12V) for battery applications.
- Low gate charge (43nC typical).
- · Fast switching speed.
- High performance trench technology for extremely low $R_{DS(ON)}$.
- High power and current handling capability.
- RoHS Compliant.





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-Source Voltage		-20	V
V _{GSS}	Gate-Source Voltage		± 12	V
I _D	Drain Current - Continuous	(Note 1a)	–11	Α
	– Pulsed		– 50	
P _D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
T _J , T _{STG}	Operating and Storage Junction Temperature Range		-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1c)	125	°C/W
R _{θJC}	Thermal Resistance, Junction-to-Case	(Note 1)	25	°C/W

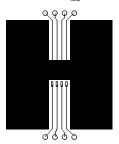
Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity	
FDS6576	FDS6576 13"		12mm	2500 units	

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics	,				
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I_D = –250 μA, Referenced to 25°C		-13		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μА
I_{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -12 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.6	-0.83	-1.5	V
$\Delta V_{GS(th)} \over \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		3.5		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = -4.5 \text{ V},$ $I_D = -11 \text{ A}$ $V_{GS} = -2.5 \text{ V},$ $I_D = -8.8 \text{ A}$ $V_{GS} = -4.5 \text{ V},$ $I_D = -11 \text{ A},$ $I_J = 125 ^{\circ}\text{C}$		8.2 11.5 11.1	14 20 23	mΩ
I _{D(on)}	On–State Drain Current	$V_{GS} = -4.5 \text{ V}, V_{DS} = -5 \text{ V}$	-25			Α
g _{FS}	Forward Transconductance	$V_{DS} = -4.5 \text{ V}, I_{D} = -11 \text{ A}$		50		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$		4044		pF
C _{oss}	Output Capacitance	f = 1.0 MHz		955		pF
C _{rss}	Reverse Transfer Capacitance			504		pF
Switchin	g Characteristics (Note 2)					
t _{d(on)}	Turn–On Delay Time	$V_{DD} = -10 \text{ V}, I_D = -1 \text{ A},$		18	32	ns
t _r	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \qquad R_{GEN} = 6 \Omega$		17	31	ns
t _{d(off)}	Turn-Off Delay Time			124	198	ns
t _f	Turn-Off Fall Time			79	126	ns
Qg	Total Gate Charge	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -11 \text{ A},$		43	60	nC
Q _{gs}	Gate-Source Charge	$V_{GS} = -4.5 V$		7		nC
Q_{gd}	Gate-Drain Charge			12		nC
Drain-So	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source	<u> </u>			-2.1	Α
V _{SD}	Drain–Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -2.1 A (Note 2)		-0.66	-1.2	V

Notes:

R_{0,1A} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of
the drain pins. R_{0,1C} is guaranteed by design while R_{0,CA} is determined by the user's board design.



a) 50°C/W when mounted on a 1in² pad of 2 oz copper



b) 105°C/W when mounted on a .04 in² pad of 2 oz copper



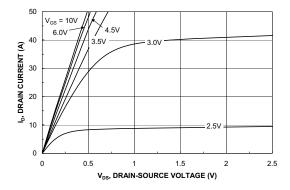
c) 125°C/W when mounted on a minimum pad.

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Scale 1:1 on letter size paper

2. Pulse Test: Pulse Width < 300μ s, Duty Cycle < 2.0%

Typical Characteristics



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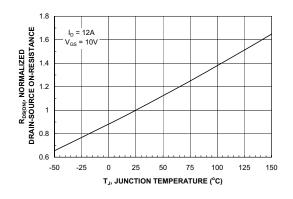
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Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



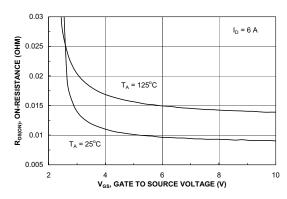
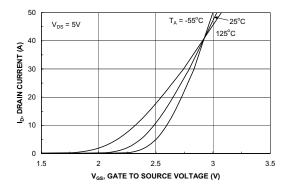


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



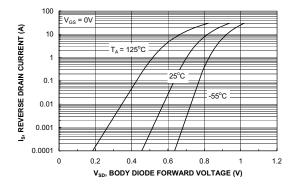
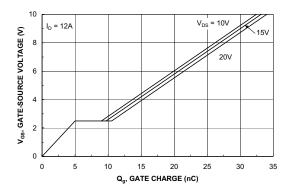


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics



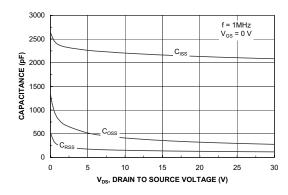
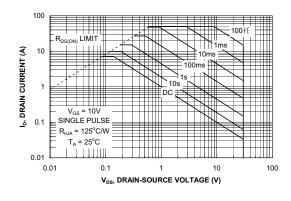


Figure 7. Gate Charge Characteristics.





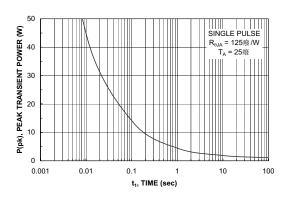


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

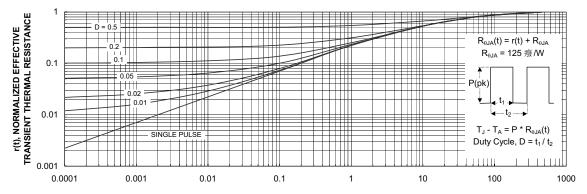


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.

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